

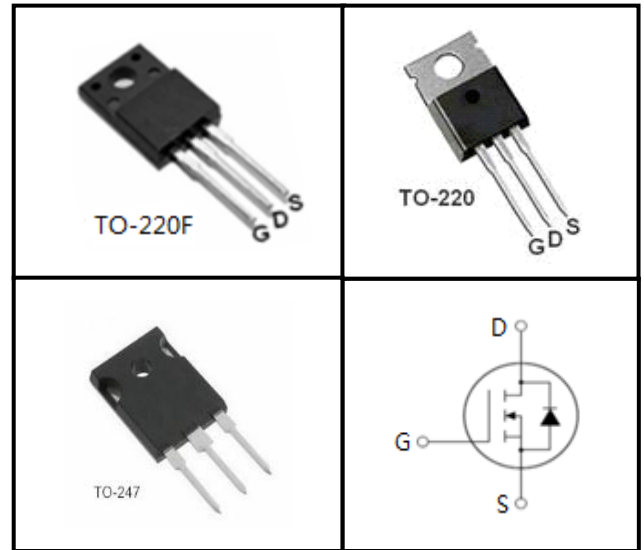
1000V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information

Device	Package	Marking
CS6N100F	TO-220F	CS6N100F
CS6N100P	TO-220	CS6N100P
CS6N100W	TO-247	CS6N100W

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value			Unit
		TO-220F	TO-220	TO-247	
Drain-Source Voltage ($V_{GS} = 0V$)	V_{DSS}	1000			V
Continuous Drain Current	I_D	6			A
Pulsed Drain Current (note1)	I_{DM}	24			A
Gate-Source Voltage	V_{GSS}	± 30			V
Single Pulse Avalanche Energy (note2)	E_{AS}	405			mJ
Avalanche Current (note1)	I_{AS}	9			A
Repetitive Avalanche Energy (note1)	E_{AR}	243			mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	65	147		W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150			$^\circ\text{C}$

Thermal Resistance

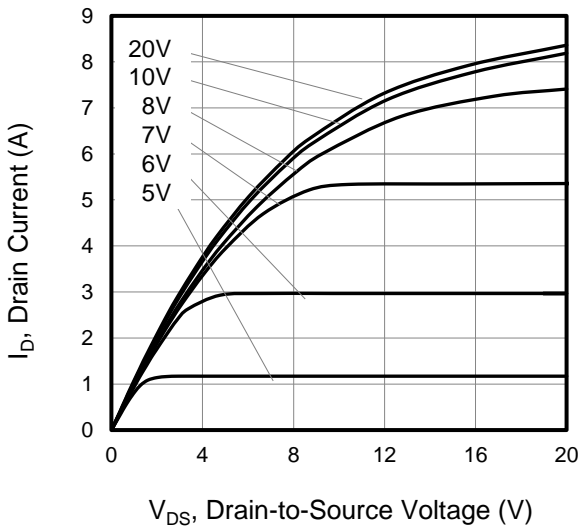
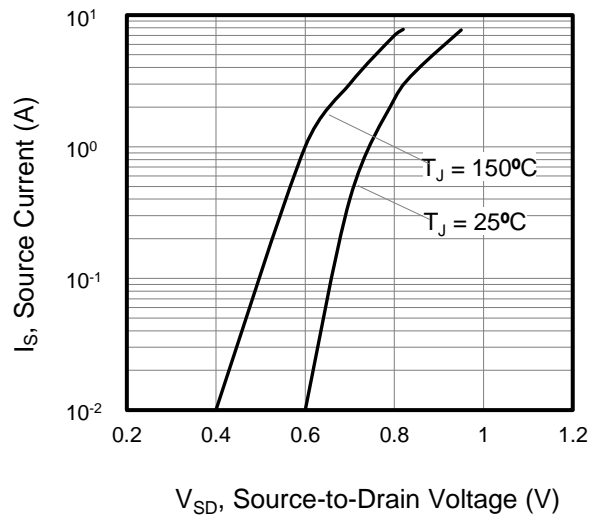
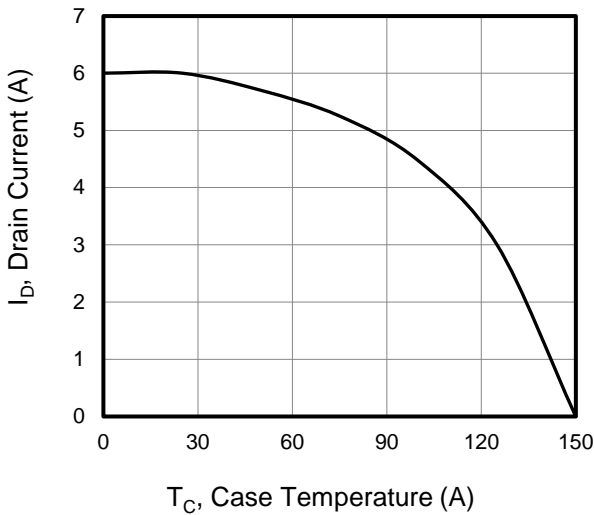
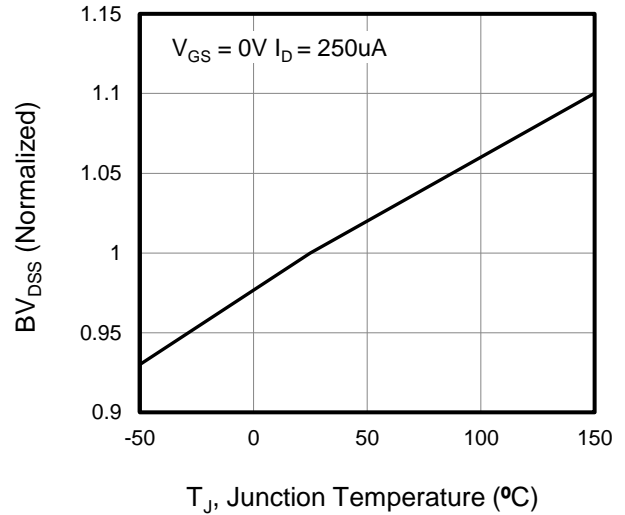
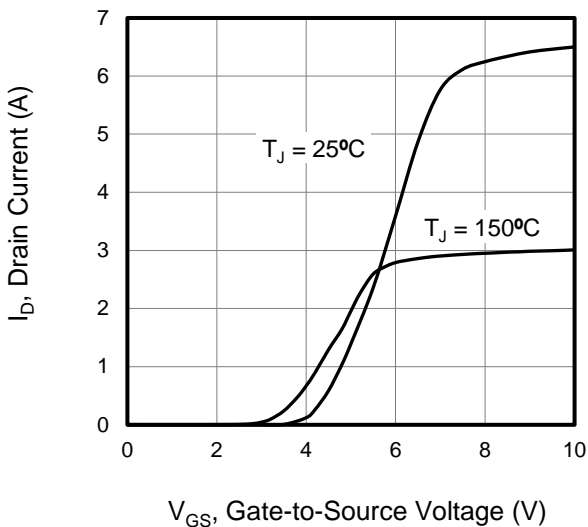
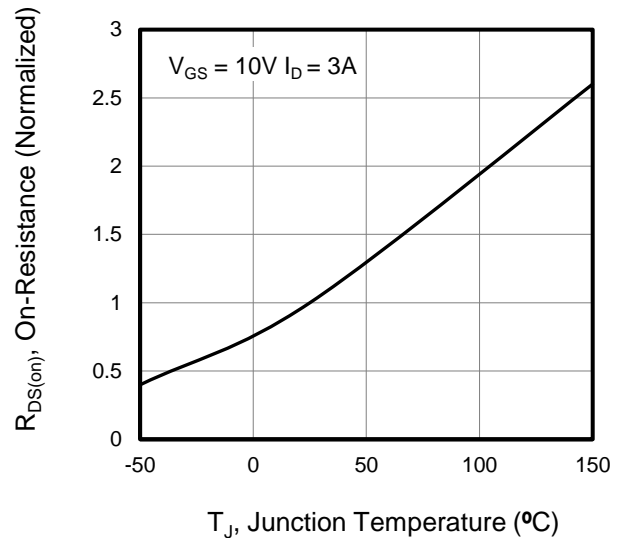
Parameter	Symbol	Value			Unit
		TO-220F	TO-220	TO-247	
Thermal Resistance, Junction-to-Case	R_{thJC}	1.92	0.85		$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62.5	60		

Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	1000	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 1000V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 3A$	--	1.2	1.5	Ω
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 1.0\text{MHz}$	--	1994	--	pF
Output Capacitance	C_{oss}		--	180	--	
Reverse Transfer Capacitance	C_{rss}		--	35	--	
Gate Resistance	R_g	$V_{GS} = 0V, V_{DS} = 0V, f = 1.0\text{MHz}$	--	0.7	--	Ω
Total Gate Charge	Q_g	$V_{DD} = 800V, I_D = 6.0A,$ $V_{GS} = 10V$	--	83	--	nC
Gate-Source Charge	Q_{gs}		--	9	--	
Gate-Drain Charge	Q_{gd}		--	46	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 500V, I_D = 6.0A,$ $R_G = 25\Omega$	--	48	--	ns
Turn-on Rise Time	t_r		--	28	--	
Turn-off Delay Time	$t_{d(off)}$		--	360	--	
Turn-off Fall Time	t_f		--	70	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	6	A
Pulsed Diode Forward Current	I_{SM}		--	--	24	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 3A, V_{GS} = 0V$	--	--	1.4	V
Reverse Recovery Time	t_{rr}	$V_R = 500V, I_S = 6A,$ $di_F/dt = 100A/\mu s$	--	541	--	ns
Reverse Recovery Charge	Q_{rr}		--	8.5	--	μC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L=10\text{mH}, V_{DD} = 70V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 1\%$

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

Figure 2. Body Diode Forward Voltage

Figure 3. Drain Current vs. Temperature

Figure 4. BV_{DSS} Variation vs. Temperature

Figure 5. Transfer Characteristics

Figure 6. On-Resistance vs. Temperature


Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Capacitance

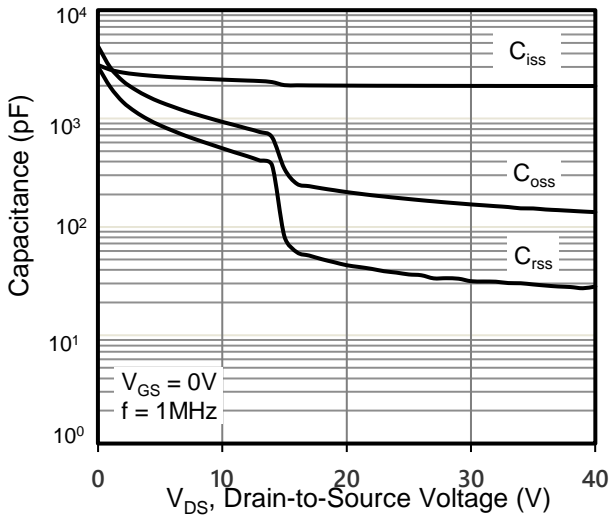


Figure 8. Gate Charge

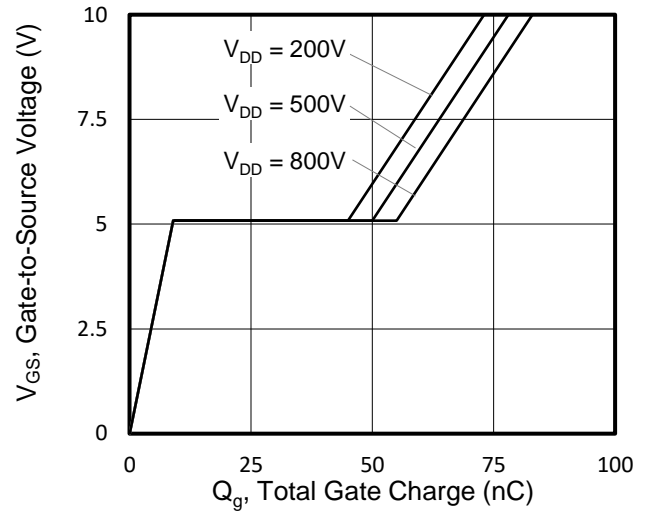


Figure 9. Transient Thermal Impedance TO-220F

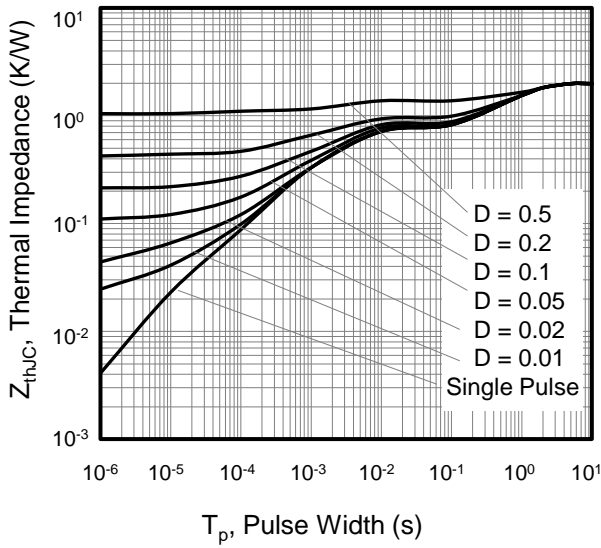


Figure 10. Transient Thermal Impedance TO-220, TO-247

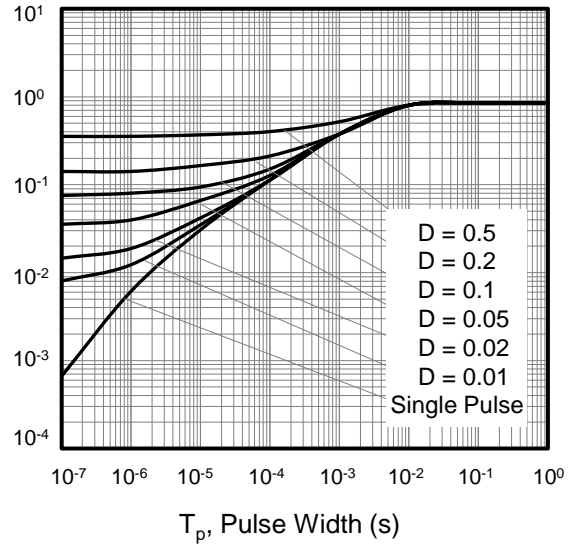


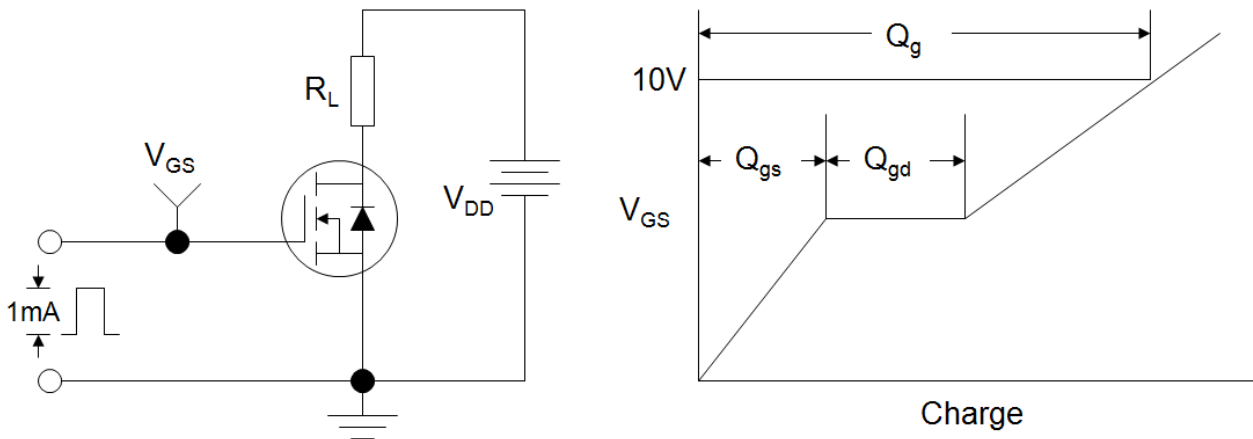
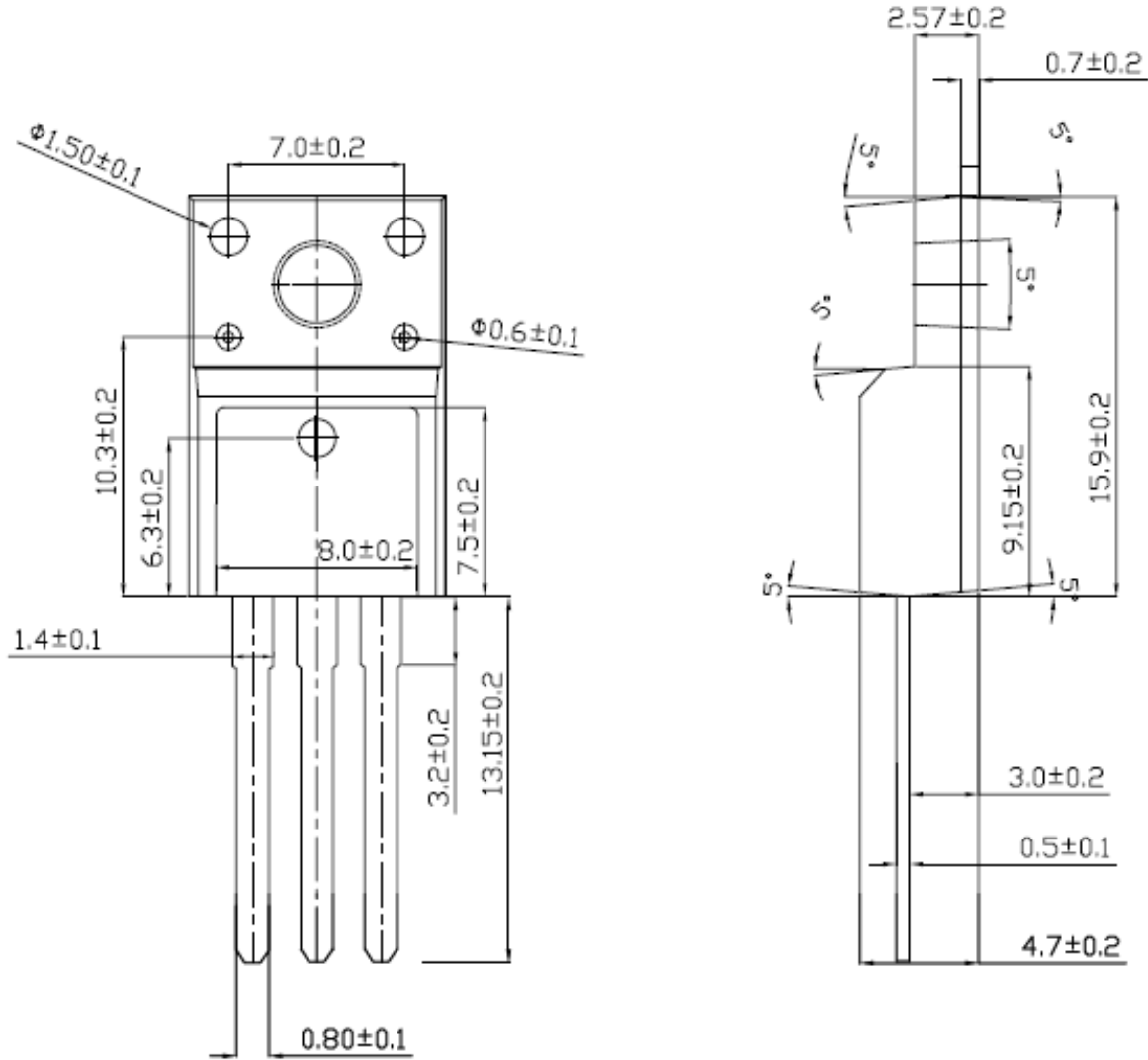
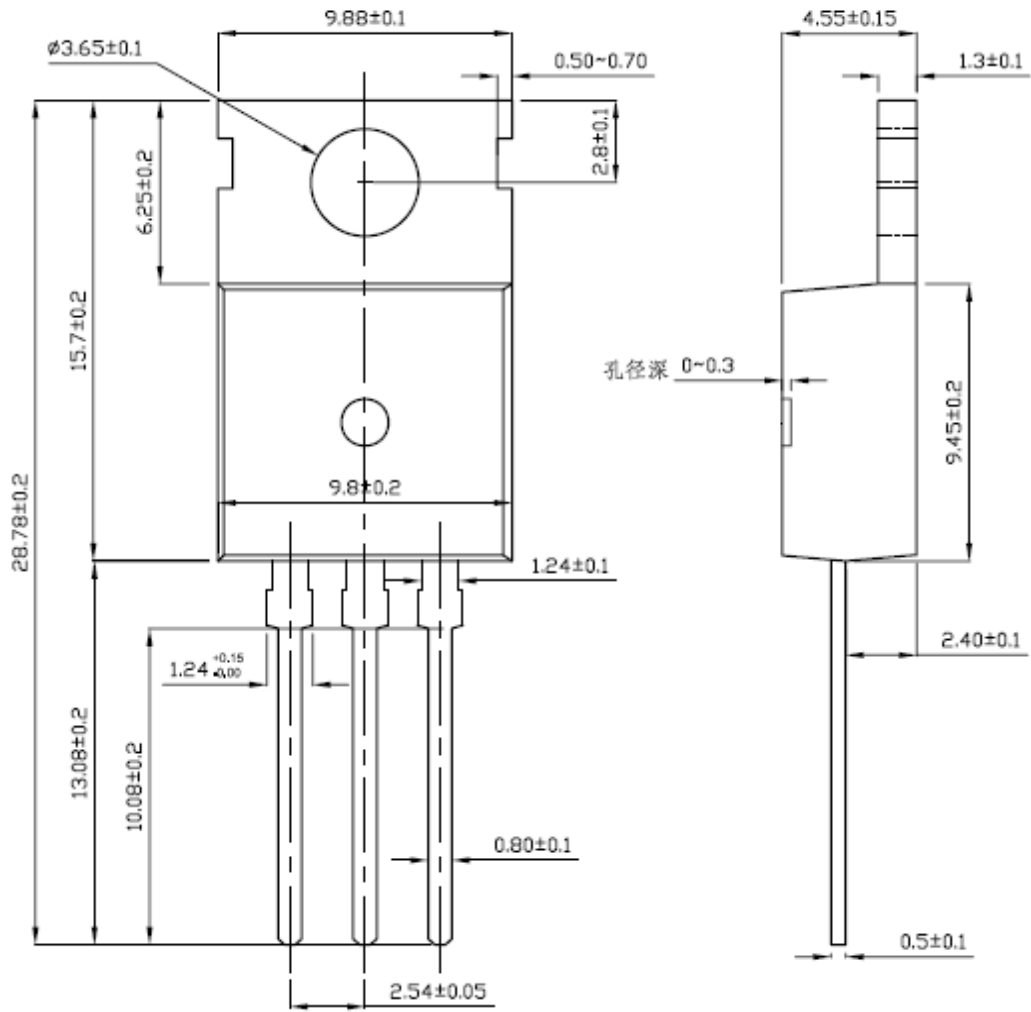
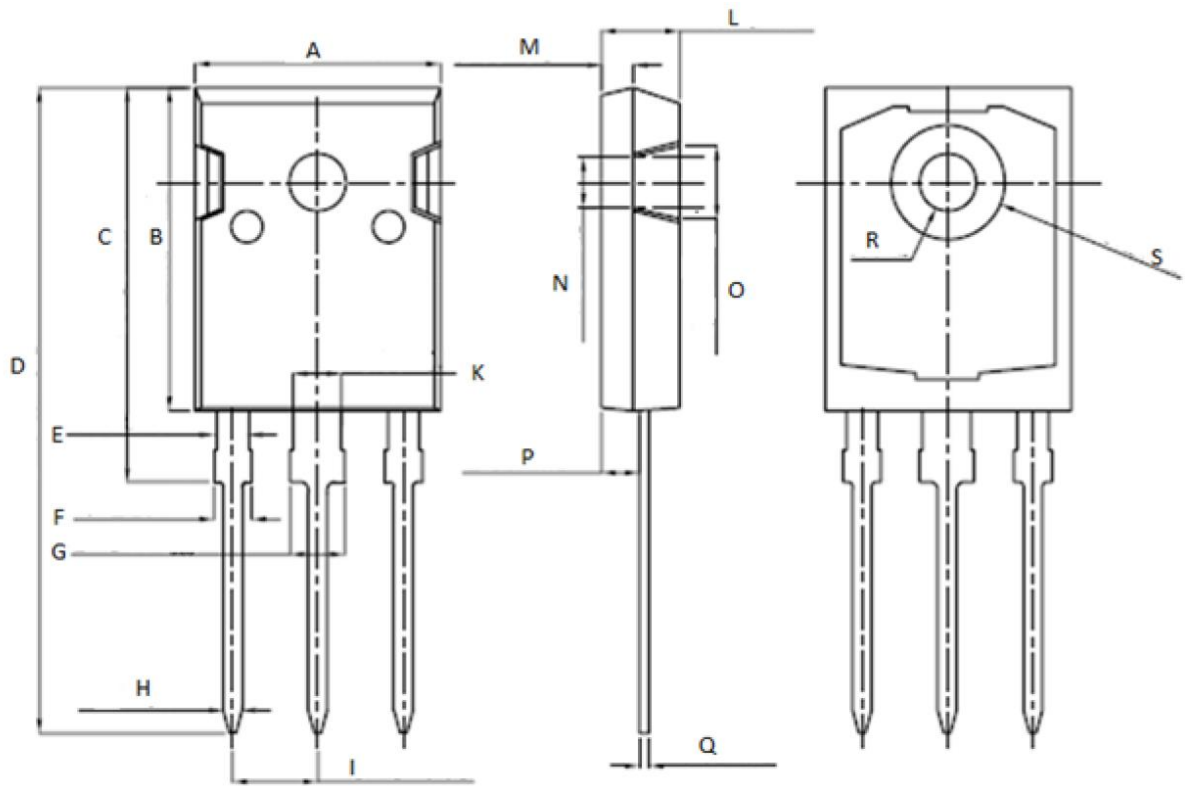
Figure A: Gate Charge Test Circuit and Waveform

Figure B: Resistive Switching Test Circuit and Waveform

Figure C: Unclamped Inductive Switching Test Circuit and Waveform


TO-220F


TO-220


TO-247


Unit: mm		
Symbol	Min.	Max.
A	15.95	16.25
B	20.85	21.25
C	20.95	21.35
D	40.5	40.9
E	1.9	2.1
F	2.1	2.25
G	3.1	3.25
H	1.1	1.3
I	5.40	5.50

Unit: mm		
Symbol	Min.	Max.
K	2.90	3.10
L	4.90	5.30
M	1.90	2.10
N	4.50	4.70
O	5.40	5.60
P	2.29	2.49
Q	0.51	0.71
R	φ 3.5	φ 3.7
S	φ 7.1	φ 7.3

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